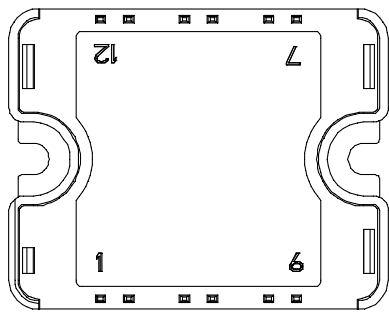
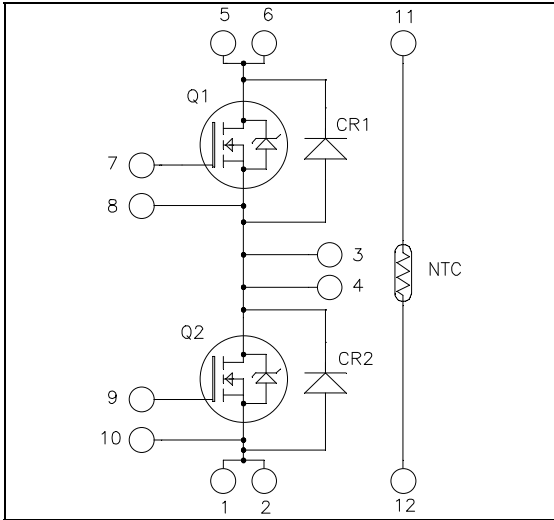


**Phase leg  
SiC MOSFET Power Module**

**$V_{DSS} = 1200V$**   
 **$R_{DS(on)} = 49m\Omega \text{ max @ } T_j = 25^\circ C$**   
 **$I_D = 55A \text{ @ } T_c = 25^\circ C$**



Pins 1/2 ; 3/4 ; 5/6 must be shorted together

**Application**

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

**Features**

- **SiC Power MOSFET**
  - Low  $R_{DS(on)}$
  - High temperature performance
- **SiC Schottky Diode**
  - Zero reverse recovery
  - Zero forward recovery
  - Temperature Independent switching behavior
  - Positive temperature coefficient on VF
- Very low stray inductance
- Internal thermistor for temperature monitoring
- High level of integration
- AlN substrate for improved thermal performance

**Benefits**

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS Compliant

**All ratings @  $T_j = 25^\circ C$  unless otherwise specified**

**1. SiC MOSFET characteristics (Per MOSFET)**

**Absolute maximum ratings**

Symbol	Parameter	Max ratings	Unit
$V_{DSS}$	Drain - Source Breakdown Voltage	1200	V
$I_D$	Continuous Drain Current	$T_c = 25^\circ C$	55
		$T_c = 80^\circ C$	42
$I_{DM}$	Pulsed Drain current	110	A
$V_{GS}$	Gate - Source Voltage	-10/+25	V
$R_{DS(on)}$	Drain - Source ON Resistance	49	m $\Omega$
$P_D$	Maximum Power Dissipation	$T_c = 25^\circ C$	250
			W

**CAUTION:** These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on [www.microsemi.com](http://www.microsemi.com)

**Electrical Characteristics**

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{GS} = 0V$ ; $V_{DS} = 1200V$		25	200	$\mu A$
$R_{DS(on)}$	Drain – Source on Resistance	$V_{GS} = 20V$ $I_D = 40A$	$T_j = 25^\circ C$	40	49	m $\Omega$
			$T_j = 150^\circ C$	75	104	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}$ ; $I_D = 2mA$	1.7	2.2		V
$I_{GSS}$	Gate – Source Leakage Current	$V_{GS} = 20V$ , $V_{DS} = 0V$			500	nA

**Dynamic Characteristics**

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$C_{iss}$	Input Capacitance	$V_{GS} = 0V$		1900		pF
$C_{oss}$	Output Capacitance	$V_{DS} = 1000V$		160		
$C_{rss}$	Reverse Transfer Capacitance	$f = 1MHz$		13		
$Q_g$	Total gate Charge	$V_{GS} = 20V$ $V_{Bus} = 800V$ $I_D = 40A$		98		nC
$Q_{gs}$	Gate – Source Charge			22		
$Q_{gd}$	Gate – Drain Charge			36		
$T_{d(on)}$	Turn-on Delay Time	$V_{GS} = -5/+20V$ $V_{Bus} = 800V$ $I_D = 40A$ $R_L = 20\Omega$ ; $R_G = 25\Omega$		12		ns
$T_r$	Rise Time			14		
$T_{d(off)}$	Turn-off Delay Time			23		
$T_f$	Fall Time			18		
$E_{on}$	Turn on Energy	Inductive Switching $V_{GS} = -5/+20V$ $V_{Bus} = 600V$ $I_D = 40A$ $R_G = 25\Omega$	$T_j = 150^\circ C$	0.9		mJ
$E_{off}$	Turn off Energy		$T_j = 150^\circ C$	0.5		mJ
$R_{thJC}$	Junction to Case Thermal Resistance				0.5	$^\circ C/W$

**2. SiC diode characteristics (Per SiC diode)**
**SiC diode ratings and characteristics**

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$V_{RRM}$	Maximum Peak Repetitive Reverse Voltage		1200			V
$I_{RM}$	Maximum Reverse Leakage Current	$V_R = 1200V$		64	400	$\mu A$
				112	2000	
$I_F$	DC Forward Current			20		A
$V_F$	Diode Forward Voltage	$I_F = 20A$	$T_j = 25^\circ C$	1.6	1.8	V
			$T_j = 175^\circ C$	2.3	3	
$Q_C$	Total Capacitive Charge	$I_F = 20A$ , $V_R = 120V$ $di/dt = 1000A/\mu s$		160		nC
$C$	Total Capacitance	$f = 1MHz$ , $V_R = 200V$		192		pF
		$f = 1MHz$ , $V_R = 400V$		138		
$R_{thJC}$	Junction to Case Thermal Resistance				0.8	$^\circ C/W$

### 3. Thermal and package characteristics

#### Package characteristics

Symbol	Characteristic	Min	Typ	Max	Unit	
V <sub>ISOL</sub>	RMS Isolation Voltage, any terminal to case t=1 min, 50/60Hz	4000			V	
T <sub>J</sub>	Operating junction temperature range	SiC MOSFET	-40	150	°C	
		SiC diode	-40	175		
T <sub>JOP</sub>	Recommended junction temperature under switching conditions	-40		T <sub>Jmax</sub> -25		
T <sub>STG</sub>	Storage Temperature Range	-40		125		
T <sub>C</sub>	Operating Case Temperature	-40		125		
Torque	Mounting torque	To heatsink	M4	2	3	N.m
Wt	Package Weight				80	g

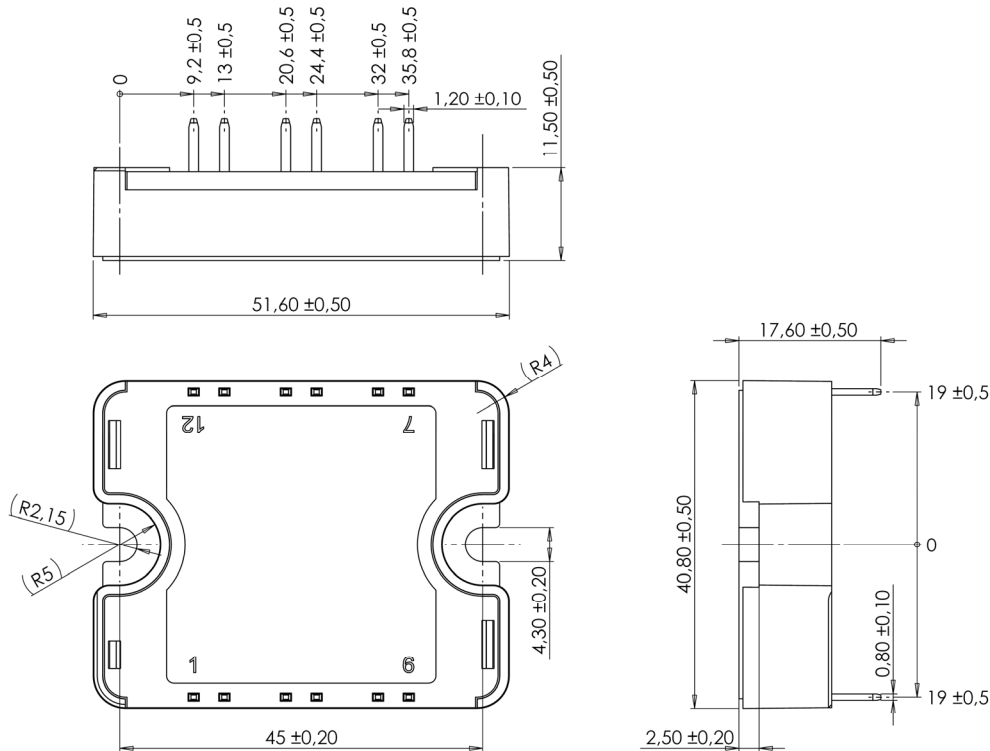
#### Temperature sensor NTC (see application note APT0406 on www.microsemi.com).

Symbol	Characteristic	Min	Typ	Max	Unit
R <sub>25</sub>	Resistance @ 25°C		50		kΩ
ΔR <sub>25</sub> /R <sub>25</sub>			5		%
B <sub>25/85</sub>	T <sub>25</sub> = 298.15 K		3952		K
ΔB/B		T <sub>C</sub> =100°C	4		%

$$R_T = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$$

T: Thermistor temperature  
R<sub>T</sub>: Thermistor value at T

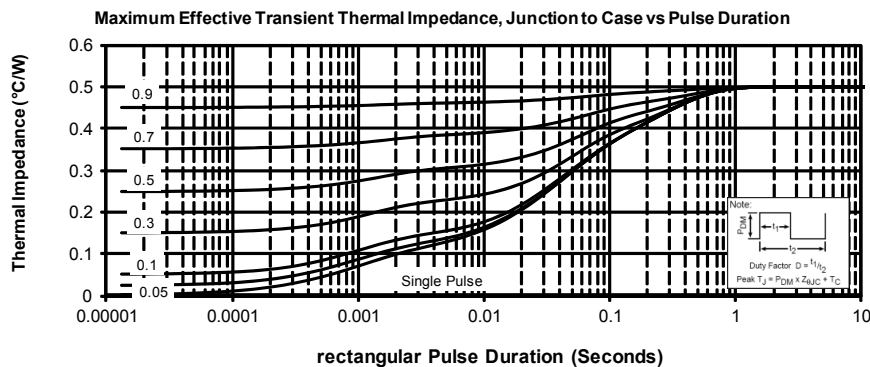
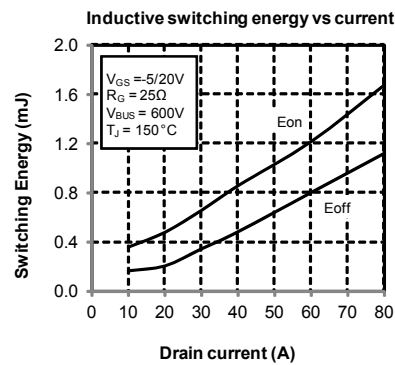
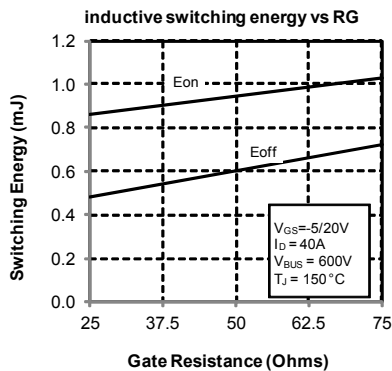
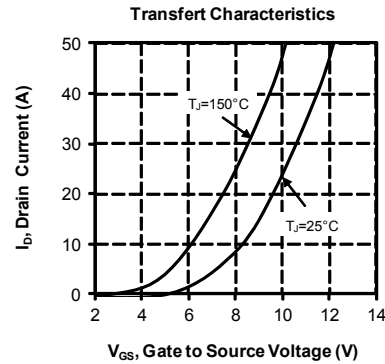
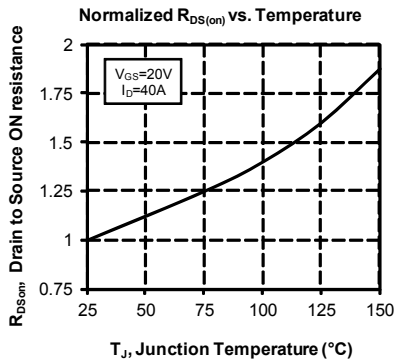
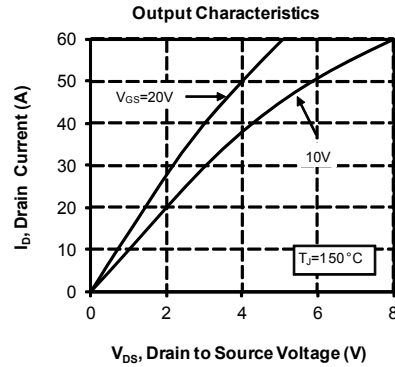
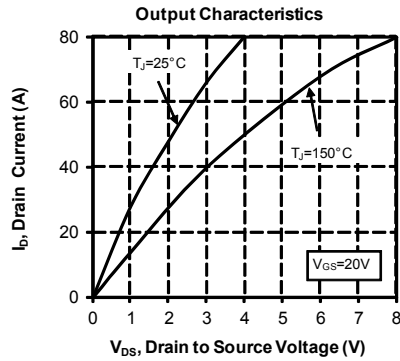
#### SP1 Package outline (dimensions in mm)

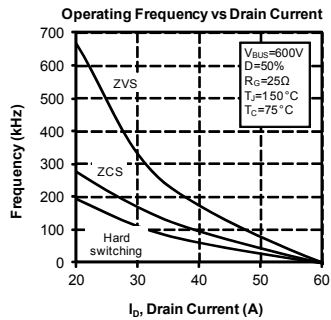
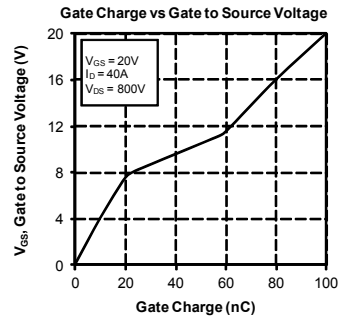
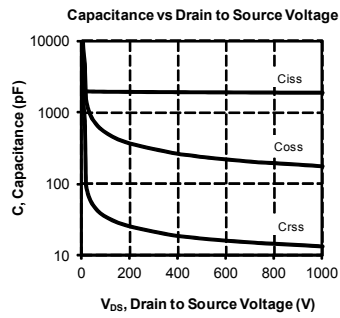


See application note 1904 - Mounting Instructions for SP1 Power Modules on www.microsemi.com

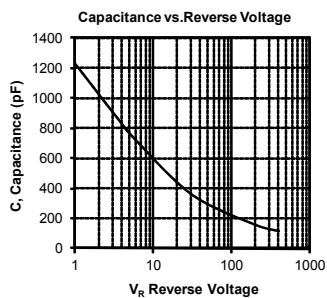
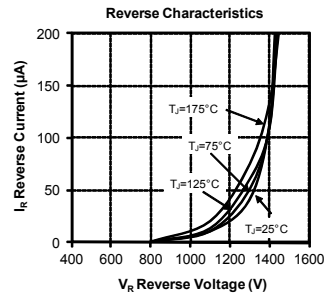
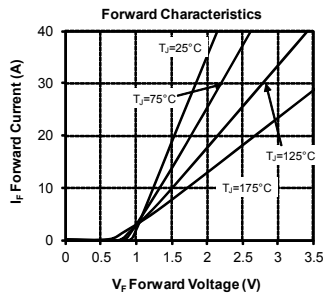
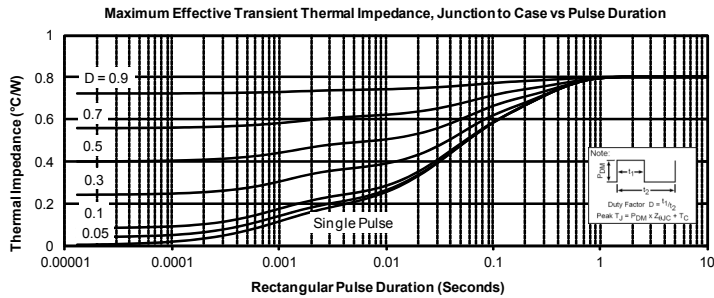
## 4. Typical Performance Curves

### SiC MOSFET





## SiC diode



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